

Hitoshi Habuka

List of Publications by Year in descending order

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156
docs citations

156
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362
citing authors

#	ARTICLE	IF	CITATIONS
1	Model on transport phenomena and epitaxial growth of silicon thin film in SiHCl ₃ -H ₂ system under atmospheric pressure. Journal of Crystal Growth, 1996, 169, 61-72.	1.5	89
2	Chemical process of silicon epitaxial growth in a SiHCl ₃ -H ₂ system. Journal of Crystal Growth, 1999, 207, 77-86.	1.5	56
3	Modeling of Epitaxial Silicon Thin-Film Growth on a Rotating Substrate in a Horizontal Single-Wafer Reactor. Journal of the Electrochemical Society, 1995, 142, 4272-4278.	2.9	37
4	Dominant rate process of silicon surface etching by hydrogen chloride gas. Thin Solid Films, 2005, 489, 104-110.	1.8	35
5	Adsorption and Desorption Rate of Multicomponent Organic Species on Silicon Wafer Surface. Journal of the Electrochemical Society, 2001, 148, G365.	2.9	33
6	Roughness of Silicon Surface Heated in Hydrogen Ambient. Journal of the Electrochemical Society, 1995, 142, 3092-3098.	2.9	32
7	Nonlinear increase in silicon epitaxial growth rate in a SiHCl ₃ -H ₂ system under atmospheric pressure. Journal of Crystal Growth, 1997, 182, 352-362.	1.5	32
8	Silicon Carbide Etching Using Chlorine Trifluoride Gas. Japanese Journal of Applied Physics, 2005, 44, 1376-1381.	1.5	32
9	Rate Theory of Multicomponent Adsorption of Organic Species on Silicon Wafer Surface. Journal of the Electrochemical Society, 2000, 147, 2319.	2.9	30
10	Silicon epitaxial growth process using trichlorosilane gas in a single-wafer high-speed substrate rotation reactor. Journal of Crystal Growth, 2011, 327, 1-5.	1.5	29
11	Temperature-Dependent Behavior of 4H-Silicon Carbide Surface Morphology Etched Using Chlorine Trifluoride Gas. Journal of the Electrochemical Society, 2009, 156, H971.	2.9	27
12	Airborne Organic Contamination Behavior on Silicon Wafer Surface. Journal of the Electrochemical Society, 2003, 150, G148.	2.9	24
13	Determination of Etch Rate Behavior of 4H-SiC Using Chlorine Trifluoride Gas. Japanese Journal of Applied Physics, 2007, 46, 7875.	1.5	24
14	Heat Transport Analysis for Flash Lamp Annealing. Japanese Journal of Applied Physics, 2007, 46, 937-942.	1.5	22
15	Numerical Evaluation of Silicon-Thin Film Growth from SiHCl ₃ -H ₂ Gas Mixture in a Horizontal Chemical Vapor Deposition Reactor. Japanese Journal of Applied Physics, 1994, 33, 1977-1985.	1.5	20
16	Development of Evaluation Method for Organic Contamination on Silicon Wafer Surfaces. Journal of the Electrochemical Society, 2001, 148, G644.	2.9	20
17	Polycrystalline silicon carbide film deposition using monomethylsilane and hydrogen chloride gases. Journal of Crystal Growth, 2007, 300, 374-381.	1.5	18
18	Silicon carbide film deposition at low temperatures using monomethylsilane gas. Surface and Coatings Technology, 2010, 204, 1432-1437.	4.8	18

#	ARTICLE	IF	CITATIONS
19	Silicon Etch Rate Using Chlorine Trifluoride. <i>Journal of the Electrochemical Society</i> , 2004, 151, G783.	2.9	17
20	In Situ Cleaning Process of Silicon Carbide Epitaxial Reactor. <i>ECS Journal of Solid State Science and Technology</i> , 2015, 4, P137-P140.	1.8	16
21	Reaction of Hydrogen Fluoride Gas at High Temperatures with Silicon Oxide Film and Silicon Surface. <i>Japanese Journal of Applied Physics</i> , 1998, 37, 6123-6127.	1.5	15
22	High-Performance Silicon Etching Using Chlorine Trifluoride Gas. <i>Journal of the Electrochemical Society</i> , 2003, 150, G461.	2.9	15
23	Time-Dependent Airborne Organic Contamination on Silicon Wafer Surface Stored in a Plastic Box. <i>Japanese Journal of Applied Physics</i> , 2003, 42, 1575-1580.	1.5	15
24	A Direct Approach for Evaluating the Thermal Condition of a Silicon Substrate under Infrared Rays and Specular Reflectors. <i>Journal of the Electrochemical Society</i> , 1999, 146, 713-718.	2.9	14
25	Cleaning Process Applicable to Silicon Carbide Chemical Vapor Deposition Reactor. <i>ECS Journal of Solid State Science and Technology</i> , 2014, 3, N3006-N3009.	1.8	14
26	Repetition of In Situ Cleaning Using Chlorine Trifluoride Gas for Silicon Carbide Epitaxial Reactor. <i>ECS Journal of Solid State Science and Technology</i> , 2016, 5, P12-P15.	1.8	14
27	In situ cleaning method for silicon surface using hydrogen fluoride gas and hydrogen chloride gas in a hydrogen ambient. <i>Journal of Crystal Growth</i> , 1998, 186, 104-112.	1.5	13
28	Dominant Forces for Driving Bubbles in a Wet Cleaning Bath Using Megasonic Wave. <i>Journal of the Electrochemical Society</i> , 2010, 157, H585.	2.9	13
29	Water Motion over a Wafer Surface Rotating in a Single-Water Wet Cleaner. <i>Journal of the Electrochemical Society</i> , 2011, 158, H487.	2.9	13
30	By-Product Formation in a Trichlorosilane-Hydrogen System for Silicon Film Deposition. <i>ECS Journal of Solid State Science and Technology</i> , 2015, 4, P16-P19.	1.8	13
31	Quartz Crystal Microbalance for Silicon Surface Organic Contamination. <i>Journal of the Electrochemical Society</i> , 2005, 152, G241.	2.9	12
32	Etch rate and surface morphology of polycrystalline β -silicon carbide using chlorine trifluoride gas. <i>Thin Solid Films</i> , 2006, 514, 193-197.	1.8	12
33	Quick Cleaning Process for Silicon Carbide Chemical Vapor Deposition Reactor. <i>ECS Journal of Solid State Science and Technology</i> , 2017, 6, P526-P530.	1.8	12
34	Metal Fluorides Produced Using Chlorine Trifluoride Gas. <i>Journal of Surface Engineered Materials and Advanced Technology</i> , 2015, 05, 228-236.	0.2	12
35	Instability of diborane gas in silicon epitaxial film growth. <i>Journal of Crystal Growth</i> , 2000, 209, 807-815.	1.5	11
36	Molecular Interaction Radii and Rate Constants for Clarifying Organic Compound Physisorption on Silicon Surface. <i>Journal of the Electrochemical Society</i> , 2010, 157, H1014.	2.9	11

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37	Mechanism of Silicon Carbide Film Deposition at Room Temperature Using Monomethylsilane Gas. Journal of the Electrochemical Society, 2011, 158, H352.	2.9	11
38	Chemical vapor deposition of amorphous silicon carbide thin films on metal surfaces using monomethylsilane gas at low temperatures. Surface and Coatings Technology, 2013, 217, 88-93.	4.8	11
39	Surface Chemical Reaction Model of Silicon Dioxide Film Etching by Dilute Hydrogen Fluoride Using a Single Wafer Wet Etcher. ECS Journal of Solid State Science and Technology, 2013, 2, P264-P267.	1.8	11
40	Water Motion in Carrierless Wet Station. Journal of the Electrochemical Society, 2004, 151, G814.	2.9	10
41	4H Silicon Carbide Etching Using Chlorine Trifluoride Gas. Materials Science Forum, 0, 600-603, 655-658.	0.3	10
42	Etching Rate of Silicon Dioxide Using Chlorine Trifluoride Gas. Japanese Journal of Applied Physics, 2009, 48, 026504.	1.5	10
43	Non-heat assistance chemical vapor deposition of amorphous silicon carbide using monomethylsilane gas under argon plasma. Surface and Coatings Technology, 2016, 285, 255-261.	4.8	10
44	Advantages of a slim vertical gas channel at high SiHCl ₃ concentrations for atmospheric pressure silicon epitaxial growth. Materials Science in Semiconductor Processing, 2018, 87, 13-18.	4.0	10
45	Gas flow and heat transfer in a pancake chemical vapor deposition reactor. Journal of Crystal Growth, 1995, 151, 375-383.	1.5	9
46	Dominant Overall Chemical Reaction in a Chlorine Trifluoride-Silicon-Nitrogen System at Atmospheric Pressure. Japanese Journal of Applied Physics, 1999, 38, 6466-6469.	1.5	9
47	Gas Velocity Influence on Silicon Surface Organic Contamination Evaluated Using Quartz Crystal Microbalance. Journal of the Electrochemical Society, 2005, 152, G862.	2.9	9
48	Physisorption and Desorption of Diethyl Phthalate and Isopropanol on a Silicon Surface. Journal of the Electrochemical Society, 2007, 154, H1031.	2.9	9
49	4H-SiC Surface Morphology Etched Using ClF ₃ Gas. Materials Science Forum, 2010, 645-648, 787-790.	0.3	9
50	Numerical calculation model of a single wafer wet etcher using a swinging nozzle. Materials Science in Semiconductor Processing, 2012, 15, 543-548.	4.0	9
51	Langasite crystal microbalance frequency behavior over wide gas phase conditions for chemical vapor deposition. Surface and Coatings Technology, 2013, 230, 312-315.	4.8	9
52	Silicon Chemical Vapor Deposition Process Using a Half-Inch Silicon Wafer for Minimal Manufacturing System. Physics Procedia, 2013, 46, 230-238.	1.2	9
53	Susceptor Coating Materials Applicable for SiC Reactor Cleaning. Materials Science Forum, 2017, 897, 99-102.	0.3	9
54	Thermal Conditions in Rapid Thermal Processing System Using Circular Infrared Lamp. Journal of the Electrochemical Society, 2000, 147, 4660.	2.9	8

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55	Design of a Rapid Thermal Processing System Using a Reflection-Resolved Ray Tracing Method. Journal of the Electrochemical Society, 2001, 148, G543.	2.9	8
56	Formation mechanism of local thickness profile of silicon epitaxial film. Journal of Crystal Growth, 2004, 266, 327-332.	1.5	8
57	Etching Rate Behavior of 4H-Silicon Carbide Using Chlorine Trifluoride Gas. ECS Transactions, 2008, 13, 39-52.	0.5	8
58	Room temperature process for chemical vapor deposition of amorphous silicon carbide thin film using monomethylsilane gas. Surface and Coatings Technology, 2011, 206, 1503-1506.	4.8	8
59	Chlorine Trifluoride Gas Transport and Etching Rate Distribution in Silicon Carbide Dry Etcher. Materials Science Forum, 0, 821-823, 553-556.	0.3	8
60	Increase in silicon film deposition rate in a SiHCl ₃ -SiH _x -H ₂ system. Journal of Crystal Growth, 2017, 468, 204-207.	1.5	8
61	Flatness Deterioration of Silicon Epitaxial Film Formed Using Horizontal Single-Wafer Epitaxial Reactor. Japanese Journal of Applied Physics, 2001, 40, 6041-6044.	1.5	7
62	Langasite Crystal Microbalance Used for In-Situ Monitoring of Amorphous Silicon Carbide Film Deposition. ECS Journal of Solid State Science and Technology, 2012, 1, P62-P65.	1.8	7
63	Density of Etch Pits on C-Face 4H-SiC Surface Produced by ClF ₃ Gas. Materials Science Forum, 0, 725, 49-52.	0.3	7
64	Development of Silicon Carbide Dry Etcher Using Chlorine Trifluoride Gas. Materials Science Forum, 0, 778-780, 738-741.	0.3	7
65	Reflector Influence on Rapid Heating of Minimal Manufacturing Chemical Vapor Deposition Reactor. ECS Journal of Solid State Science and Technology, 2016, 5, P280-P284.	1.8	7
66	Mirror Etching of Single Crystalline C-Face 4H-Silicon Carbide Wafer by Chlorine Trifluoride Gas. ECS Journal of Solid State Science and Technology, 2017, 6, P582-P585.	1.8	7
67	Exposure of Tantalum Carbide, Silicon Nitride and Aluminum Nitride to Chlorine Trifluoride Gas. ECS Journal of Solid State Science and Technology, 2019, 8, P175-P179.	1.8	7
68	Haze Generation on Silicon Surface Heated in Hydrogen Ambient at Atmospheric Pressure. Journal of the Electrochemical Society, 1997, 144, 3261-3265.	2.9	6
69	Change in Microroughness of a Silicon Surface during In Situ Cleaning Using HF and HCl Gases. Journal of the Electrochemical Society, 1998, 145, 4264-4271.	2.9	6
70	Model of boron incorporation into silicon epitaxial film in a B ₂ H ₆ -SiHCl ₃ -H ₂ system. Journal of Crystal Growth, 2001, 222, 183-193.	1.5	6
71	Flatness Deterioration of Silicon Epitaxial Film Formed in a Horizontal Single-Wafer Epitaxial Reactor II. Japanese Journal of Applied Physics, 2002, 41, 5692-5696.	1.5	6
72	Density and Behavior of Etch Pits on C-Face 4H-SiC Surface Produced by ClF ₃ Gas. Materials Science Forum, 2012, 717-720, 379-382.	0.3	6

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73	Transport phenomena in a slim vertical atmospheric pressure chemical vapor deposition reactor utilizing natural convection. <i>Materials Science in Semiconductor Processing</i> , 2017, 71, 348-351.	4.0	6
74	Non-Heat Assistance Plasma-Enhanced Chemical Vapor Deposition of SiC _x NyOz Film Using Monomethylsilane, Nitrogen and Argon. <i>ECS Journal of Solid State Science and Technology</i> , 2017, 6, P443-P448.	1.8	6
75	Real time evaluation of silicon epitaxial growth process by exhaust gas measurement using quartz crystal microbalance. <i>Materials Science in Semiconductor Processing</i> , 2018, 88, 192-197.	4.0	6
76	Deposition and etching behaviour of boron trichloride gas at silicon surface. <i>Journal of Crystal Growth</i> , 2020, 529, 125301.	1.5	6
77	Slim Water Injection Nozzle for Silicon Wafer Wet Cleaning Bath. <i>Advances in Chemical Engineering and Science</i> , 2016, 06, 345-354.	0.5	6
78	Effect of Transport Phenomena on Boron Concentration Profiles in Silicon Epitaxial Wafers. <i>Journal of the Electrochemical Society</i> , 1996, 143, 677-682.	2.9	5
79	Hot-wall and cold-wall environments for silicon epitaxial film growth. <i>Journal of Crystal Growth</i> , 2001, 223, 145-155.	1.5	5
80	Heat Balance Evaluation for Rapid Thermal Processing System Design. <i>Journal of the Electrochemical Society</i> , 2005, 152, G924.	2.9	5
81	Decarbonation and Pore Structural Change of Ca-Solid Reactant for CaO/CO ₂ Chemical Heat Pump. <i>Journal of Chemical Engineering of Japan</i> , 2008, 41, 513-518.	0.6	5
82	Langasite Crystal Microbalance for Development of Reactive Surface Preparation of Silicon Carbide Film Deposition from Monomethylsilane Gas. <i>Japanese Journal of Applied Physics</i> , 2011, 50, 096505.	1.5	5
83	Surface and gas phase reactions induced in a trichlorosilane-SiH _x system for silicon film deposition. <i>Surface and Coatings Technology</i> , 2015, 272, 273-277.	4.8	5
84	In Situ Measurement for Evaluating Temperature Change Related to Silicon Film Formation in a SiHCl ₃ -H ₂ System. <i>ECS Journal of Solid State Science and Technology</i> , 2016, 5, P16-P20.	1.8	5
85	A Method to Adjust Polycrystalline Silicon Carbide Etching Rate Profile by Chlorine Trifluoride Gas. <i>Materials Science Forum</i> , 0, 897, 383-386.	0.3	5
86	Parallel langmuir processes for silicon epitaxial growth in a SiHCl ₃ -SiH _x -H ₂ system. <i>Materials Science in Semiconductor Processing</i> , 2017, 72, 134-138.	4.0	5
87	Yttrium oxide film for protecting quartz glass surface from etching by long-term exposure to chlorine trifluoride gas at room temperature. <i>Materials Science in Semiconductor Processing</i> , 2018, 83, 211-215.	4.0	5
88	Nonempirical Design of Rapid Thermal Processing System. <i>Japanese Journal of Applied Physics</i> , 2001, 40, 7123-7128.	1.5	4
89	<i>in situ</i> observation of chemical vapor deposition using SiHCl ₃ and BCl ₃ gases. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015, 12, 953-957.	0.8	4
90	Evaluation of Molecular Interaction between Organic Molecules Physisorbed on Silicon Native Oxide Surface in Dry and Humid Atmosphere. <i>ECS Journal of Solid State Science and Technology</i> , 2015, 4, P86-P90.	1.8	4

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91	Formation and Removal of Carbon Film on Silicon Carbide Surface Using Chlorine Trifluoride Gas. ECS Journal of Solid State Science and Technology, 2016, 5, P441-P445.	1.8	4
92	High-Temperature Reactor Cleaning Using Chlorine Trifluoride Gas for Silicon Carbide Chemical Vapor Deposition. ECS Journal of Solid State Science and Technology, 2019, 8, P400-P406.	1.8	4
93	Anticorrosive Behavior of SiC _x N _y O _z Film Formed by Non-Heat Assistance Plasma-Enhanced Chemical Vapor Deposition Using Monomethylsilane, Nitrogen and Argon Gases. ECS Journal of Solid State Science and Technology, 2020, 9, 024001.	1.8	4
94	Boron-Silicon Film Chemical Vapor Deposition Using Boron Trichloride, Dichlorosilane and Monomethylsilane Gases. ECS Journal of Solid State Science and Technology, 2021, 10, 064006.	1.8	4
95	Design of a Silicon Carbide Chemical Vapor Deposition Reactor Cleaning Process Using Chlorine Trifluoride Gas Accounting for Exothermic Reaction Heat. ECS Journal of Solid State Science and Technology, 2020, 9, 104008.	1.8	4
96	Computation Transport Phenomena in Chemical Engineering. Transport of Dopant Gas during Silicon Epitaxial Thin-Film Growth in a Horizontal Reactor.. Kagaku Kogaku Ronbunshu, 1997, 23, 772-779.	0.3	3
97	Highly Concentrated Ozone Gas for Preparing Wettable Polyimide Surface. Japanese Journal of Applied Physics, 2005, 44, 5225-5230.	1.5	3
98	Water and Bubble Motions Under Megasonic Wave in a Silicon Wafer Wet Cleaning Bath. ECS Transactions, 2009, 25, 265-272.	0.5	3
99	Low Temperature SiC Film Deposition Using Trichlorosilane Gas and Monomethylsilane Gas. Journal of Nanoscience and Nanotechnology, 2011, 11, 8374-8377.	0.9	3
100	Precipitates caused by prolonged high-temperature annealing in floating zone silicon wafer grown from Czochralski single-crystal rod. Materials Science in Semiconductor Processing, 2013, 16, 923-927.	4.0	3
101	Numerical evaluation of silicon epitaxial growth on a 450mm diameter substrate. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1539-1543.	1.8	3
102	Cleaning Process for Using Chlorine Trifluoride Gas Silicon Carbide Chemical Vapor Deposition Reactor. Materials Science Forum, 2015, 821-823, 125-128.	0.3	3
103	Water Outlet Design of Wet Cleaning Bath for 300-mm Diameter Silicon Wafers. ECS Journal of Solid State Science and Technology, 2018, 7, N123-N127.	1.8	3
104	Influence of Metal and Polymer Substrate on SiC _x N _y O _z Film Formation by Non-Heat Assistance Plasma-Enhanced Chemical Vapor Deposition Using Monomethylsilane, Nitrogen and Argon Gases. ECS Journal of Solid State Science and Technology, 2019, 8, P407-P411.	1.8	3
105	Chlorine Trifluoride Gas Distributor Design for Single-Crystalline C-Face 4H-Silicon Carbide Wafer Etcher. Materials Science Forum, 0, 963, 520-524.	0.3	3
106	CVD Material Processing. Numerical Calculations of Heat Profile using Circular Infrared Lamp Heating Furnace.. Kagaku Kogaku Ronbunshu, 2000, 26, 785-791.	0.3	2
107	Air Flow in Square Quartz Plate Spin Cleaner. Japanese Journal of Applied Physics, 2005, 44, 8182-8185.	1.5	2
108	Small-Batch Reactor Development for Silicon Epitaxial Film Growth Based on Theory of Transport Phenomena. ECS Transactions, 2006, 2, 21-32.	0.5	2

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109	Carbonation/Decarbonation of Ca-Solid Reactant Derived from Natural Limestone for Thermal-Energy Storage and Temperature Upgrade. Journal of Chemical Engineering of Japan, 2007, 40, 1270-1274.	0.6	2
110	Heat Transport and Temperature Gradient in Silicon-on-Insulator Wafer during Flash Lamp Annealing Process. Japanese Journal of Applied Physics, 2008, 47, 6277-6281.	1.5	2
111	Hafnium Oxide Film Etching Using Hydrogen Chloride Gas. Japanese Journal of Applied Physics, 2009, 48, 125503.	1.5	2
112	Etch Pits on 4H-SiC Surface Produced by ClF_3 Gas. Materials Science Forum, 0, 679-680, 286-289.	0.3	2
113	Water Motion over a Wafer Surface Rotating in a Single-Wafer Wet Cleaner. ECS Transactions, 2011, 41, 279-286.	0.5	2
114	Silicon Epitaxial Growth Rate and Transport Phenomena in a Vertical Stacked-Type Multi-Wafer Reactor. Japanese Journal of Applied Physics, 2012, 51, 026701.	1.5	2
115	Off-Orientation Influence on C-Face (0001) 4H-SiC Surface Morphology Produced by Etching Using Chlorine Trifluoride Gas. ECS Journal of Solid State Science and Technology, 2013, 2, N3025-N3027.	1.8	2
116	Precipitates formed in silicon wafers by prolonged high-temperature annealing in nitrogen atmosphere. Japanese Journal of Applied Physics, 2014, 53, 05FJ05.	1.5	2
117	Silicon epitaxial growth accelerated by parallel Langmuir processes using SiH_2Cl_2 and SiH_3CH_3 gases. Semiconductor Science and Technology, 2018, 33, 094002.	2.0	2
118	Quartz crystal microbalance for real-time monitoring chlorosilane gas transport in slim vertical cold wall chemical vapor deposition reactor. Materials Science in Semiconductor Processing, 2020, 106, 104759.	4.0	2
119	Etching Rate Profile of C-Face 4H-SiC Wafer Depending on Total Gas Flow Rate of Chlorine Trifluoride and Nitrogen. Materials Science Forum, 0, 1004, 173-179.	0.3	2
120	Electric Current in Rate Equation for Parallel Plate Plasma-Enhanced Chemical Vapour Deposition of $\text{SiC}_x\text{N}_y\text{O}_z$ Film without Heat Assistance. ECS Journal of Solid State Science and Technology, 2020, 9, 024017.	1.8	2
121	Benzoxazine-modified BMI Heat-resistant Resin with Low Dielectric Properties. Transactions of the Japan Institute of Electronics Packaging, 2021, 14, E20-016-1-E20-016-14.	0.4	2
122	Langasite Crystal Microbalance for Development of Reactive Surface Preparation of Silicon Carbide Film Deposition from Monomethylsilane Gas. Japanese Journal of Applied Physics, 2011, 50, 096505.	1.5	2
123	A Practical Design Method for a Rapid Thermal Processing System. Japanese Journal of Applied Physics, 2004, 43, 833-838.	1.5	1
124	Room Temperature Halogenation of Polyimide Film Surface using Chlorine Trifluoride Gas. Japanese Journal of Applied Physics, 2004, 43, 730-734.	1.5	1
125	In-Situ Measurement Method and Rate Theory for Clarifying Multi-Component Organic Compounds Adsorption and Desorption on Silicon Surface. ECS Transactions, 2007, 11, 363-374.	0.5	1
126	Hafnium Oxide Etching Using Hydrogen Chloride Gas. ECS Transactions, 2009, 19, 289-299.	0.5	1

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127	Atmospheric Pressure SiC Film Deposition at Low Temperatures Using SiH ₃ CH ₃ and HCl Gases. ECS Transactions, 2009, 25, 191-198.	0.5	1
128	Room Temperature Process for Chemical Vapor Deposition of Amorphous Silicon Carbide Thin Film Using Monomethylsilane Gas. Materials Research Society Symposia Proceedings, 2012, 1433, 83.	0.1	1
129	Low temperature amorphous silicon carbide thin film formation process on aluminum surface using monomethylsilane gas and trichlorosilane gas. Journal of Crystal Growth, 2014, 401, 523-526.	1.5	1
130	In Situ Method for Determining Combination of Organic Compounds Interacting with Each Other on Silicon Oxide Surface. ECS Journal of Solid State Science and Technology, 2015, 4, P408-P414.	1.8	1
131	4H-Silicon Carbide Wafer Surface after Chlorine Trifluoride Gas Etching. Materials Science Forum, 0, 924, 369-372.	0.3	1
132	High Temperature SiC Reactor Cleaning Using Chlorine Trifluoride Gas Achieved by Purified Pyrolytic Carbon Coating Film. Materials Science Forum, 0, 963, 141-145.	0.3	1
133	Non-Plasma Dry Etcher Design for 200 mm-Diameter Silicon Carbide Wafer. Materials Science Forum, 0, 1004, 167-172.	0.3	1
134	Development of SiC Etching by Chlorine Fluoride Gas. Materials Science Forum, 0, 1004, 731-737.	0.3	1
135	Side wall water outlet design for silicon wafer wet cleaning bath. Materials Science in Semiconductor Processing, 2020, 110, 104970.	4.0	1
136	Temperature Influence on Organic Molecular Interaction on Silicon Oxide Surface In Situ Measured Utilizing a Quartz Crystal Microbalance. ECS Journal of Solid State Science and Technology, 2020, 9, 104007.	1.8	1
137	Room Temperature and Reduced Pressure Chemical Vapor Deposition of Silicon Carbide on Various Materials Surface. Advances in Chemical Engineering and Science, 2014, 04, 389-395.	0.5	1
138	Behavior of Viscous Liquid Byproduct Formed in Exhaust Tube by Silicon Carbide Epitaxial Growth. ECS Journal of Solid State Science and Technology, 2019, 8, P805-P810.	1.8	1
139	Water Motion in a Water Curtain Head for Cleaning a Large Glass Plate. Japanese Journal of Applied Physics, 2007, 46, 838-842.	1.5	0
140	Low Temperature Chemical Vapour Deposition of Polycrystalline Silicon Carbide Film Using Monomethylsilane Gas. , 0, , .		0
141	Silicon Surface Morphology after Annealing in Ambient Hydrogen Containing a Trace Amount of Hydrogen Halide Gas. Japanese Journal of Applied Physics, 2011, 50, 025701.	1.5	0
142	Concentration of Three Organic Compounds Influencing each other on Silicon Surface. Solid State Phenomena, 2012, 187, 303-306.	0.3	0
143	Crystalline Defects in Silicon Wafer Caused by Prolonged High-Temperature Annealing in Nitrogen Atmosphere. Advanced Materials Research, 2013, 699, 445-449.	0.3	0
144	Amorphous Silicon Carbide Film Formation at Room Temperature by Monomethylsilane Gas. Materials Science Forum, 0, 740-742, 235-238.	0.3	0

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145	Off-Orientation Influence on C-Face (0001) 4H-SiC Surface Morphology Produced by Etching Using Chlorine Trifluoride Gas. Materials Science Forum, 2014, 778-780, 734-737.	0.3	0
146	Precipitates Caused in Silicon Wafers by Prolonged High-Temperature Annealing in Nitrogen Atmosphere. Materials Research Society Symposia Proceedings, 2014, 1591, 1.	0.1	0
147	In Situ Observation of Chemical Vapour Deposition Using Langasite Crystal Microbalance. , 0, , .		0
148	Quick and Practical Cleaning Process for Silicon Carbide Epitaxial Reactor. Materials Science Forum, 0, 924, 96-99.	0.3	0
149	Silicon Epitaxial Reactor for Minimal Fab. , 2018, , .		0
150	SiC Epitaxial Reactor Cleaning by ClF_3 Gas with the Help of Reaction Heat. Materials Science Forum, 0, 1004, 186-192.	0.3	0
151	Anticorrosive Behavior of Aluminum Nitride Surface Exposed to Chlorine Trifluoride Gas at High Temperatures. ECS Journal of Solid State Science and Technology, 2021, 10, 034006.	1.8	0
152	Chemical Conditions of SiCNO Film Exposed to ClF_3 Gas. ECS Journal of Solid State Science and Technology, 2021, 10, 103004.	1.8	0
153	Advance of Atomic Layer Deposition in Semiconductor Materials Manufacturing Process: Cleaning Technology for Thin Film Formation Reactor. Journal of the Vacuum Society of Japan, 2011, 54, 97-104.	0.3	0
154	Silicon Surface Morphology after Annealing in Ambient Hydrogen Containing a Trace Amount of Hydrogen Halide Gas. Japanese Journal of Applied Physics, 2011, 50, 025701.	1.5	0
155	Silicon Epitaxial Growth Rate and Transport Phenomena in a Vertical Stacked-Type Multi-Wafer Reactor. Japanese Journal of Applied Physics, 2012, 51, 026701.	1.5	0
156	Water Flow Improvement by Pinhole Outlet in Batch-Type Wet Cleaning Bath for Large-Diameter Wafers. ECS Journal of Solid State Science and Technology, 0, , .	1.8	0